Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9. (Canceled)

10. (Currently Amended) A method for producing a single crystal by Czochralski method by pulling a seed crystal from a raw material melt, comprising:

immersing the seed crystal into the raw material melt; and

growing the single crystal by rotating and pulling the seed crystal,

wherein:

the single crystal is pulled while controlling a value of V/G ($mm^2/K \cdot min$) within a range of values of V/G ($mm^2/K \cdot min$); and

the range of values of V/G ($mm^2/K \cdot min$), including a defect region and/or a defect-free region, is controlled according to Tmax (°C);

wherein:

V(mm/min) is a single crystal pulling rate of pulling the single crystal;

G (K/mm) is a temperature gradient at a solid-liquid interface, in a range of a melting point of the raw material and 1400°C;

Tmax (°C) is a highest temperature of the raw material melt at an interface between a quartz crucible inner wall and the raw material melt; and

the range of values of V/G ($mm^2/K \cdot min$) is ~~selected from the group consisting of~~:

(A) from $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.31$ ($mm^2/K \cdot min$) to less than $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.38$ ($mm^2/K \cdot min$); or

(B) $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.38$ ($mm^2/K \cdot min$) or more; ~~and~~ or

(C) from $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.31$ ($mm^2/K \cdot min$) to $-0.000724\ [mm^2/(°C \cdot K \cdot min)] \times Tmax\ (°C) + 1.35$ ($mm^2/K \cdot min$).

11-13. (Canceled)

14. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the Tmax (°C) being in a range of 1560 °C or less.

15-17. (Canceled)

18. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19-21. (Canceled)

22. (Previously Presented) The method for producing a single crystal according to Claim 14, wherein, at least, the Tmax (°C) is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23-25. (Canceled)

26. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein the single crystal that is pulled is a silicon single crystal.

27. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein the single crystal that is pulled has a diameter of 200mm or more.

28. (Canceled)